

XP-002167343

AN - 1997-347912 [32]

AP - JP19950331110 19951127

CPY - HITK

DC - M13 P55

FS - CPI;GMPI

IC - B23K20/00 ; C23C14/34

MC - M13-G02

PA - (HITK) HITACHI METALS LTD

PN - JP9143704 A 19970603 DW199732 C23C14/34 001pp

PR - JP19950331110 19951127

XA - C1997-112372

XIC - B23K-020/00 ; C23C-014/34

XP - N1997-288352

AB - J09143704 The Ti-target is made by isostatic pressing Ti-target material and backing plate mainly of Al in contact state at 300-450 deg. C with a pressure of 50-200 MPa, to obtain a target material which is cemented by diffusing the target material having recrystallised structure of maximum grain size of up to 20 mu m. and mean crystal grain size of up to 10 mu m. and the backing plate.

- USE - For forming thin film contg. Ti by sputtering.

- (Dwg.0/2)

IW - TITANIUM TARGET MANUFACTURE SPUTTER ISOSTATIC PRESS TITANIUM TARGET MATERIAL BACKING PLATE ALUMINIUM SPECIFIC PRESSURE

IKW - TITANIUM TARGET MANUFACTURE SPUTTER ISOSTATIC PRESS TITANIUM TARGET MATERIAL BACKING PLATE ALUMINIUM SPECIFIC PRESSURE

NC - 001

OPD - 1995-11-27

ORD - 1997-06-03

PAW - (HITK) HITACHI METALS LTD

TI - Titanium target manufacture for sputtering - by isostatic pressing titanium target material and backing plate of aluminium at specific pressure etc